September 2005

QFET ®

FAIRCHILD SEMICONDUCTOR®

FQA8N100C 1000V N-Channel MOSFET

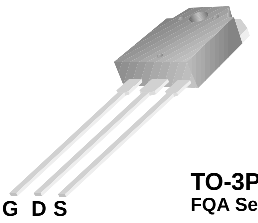
Features

- 8A, 1000V, $R_{DS(on)}$ = 1.45Ω @V_{GS} = 10 V
- Low gate charge (typical 53 nC)
- Low C_{rss} (typical 16 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

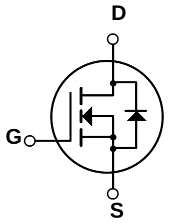
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies.



TO-3PN
FQA Series



Absolute Maximum Ratings

Symbol	Parameter	FQA8N100C	Unit
V_{DSS}	Drain-Source Voltage	1000	V
I_D	Drain Current - Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	8 5	A A
I_{DM}	Drain Current - Pulsed (Note 1)	32	A
V_{GSS}	Gate-Source voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	850	mJ
I_{AR}	Avalanche Current (Note 1)	8	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	22.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation (T_C = 25°C) - Derate above 25°C	225 1.79	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.56	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA8N100C	FQA8N100C	TO-3PN	--	--	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA	1000	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250µA, Referenced to 25°C	--	1.4	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 1000V, V_{GS} = 0V V_{DS} = 800V, T_C = 125°C	-- --	-- --	10 100	µA µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 4A	--	1.2	1.45	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50V, I_D = 4A (Note 4)	--	8.0	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	2475	3220	pF
C_{oss}	Output Capacitance		--	195	255	pF
C_{rss}	Reverse Transfer Capacitance		--	16	24	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 500V, I_D = 8A R_G = 25Ω (Note 4, 5)	--	50	110	ns
t_r	Turn-On Rise Time		--	95	200	ns
$t_{d(off)}$	Turn-Off Delay Time		--	122	254	ns
t_f	Turn-Off Fall Time		--	80	170	ns
Q_g	Total Gate Charge	V_{DS} = 800V, I_D = 8A V_{GS} = 10V (Note 4, 5)	--	53	70	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		--	23	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	32	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 8A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 8A dI_F/dt =100A/µs (Note 4)	--	620	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.2	--	µC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 25mH, I_{AS} = 8A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. $I_{SD} \leq$ 8A, di/dt $\leq$ 200A/µs, $V_{DD} \leq BV_{DSS}$, Starting T_J = 25°C
4. Pulse Test: Pulse width $\leq$ 300µs, Duty Cycle $\leq$ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

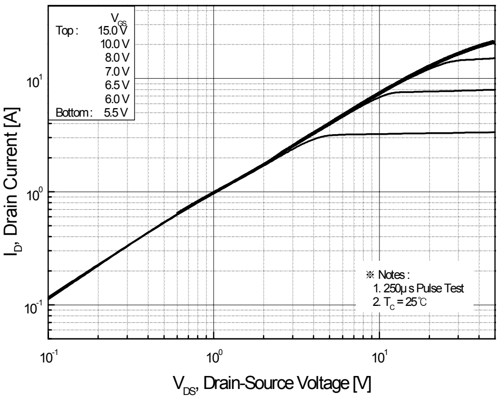


Figure 2. Transfer Characteristics

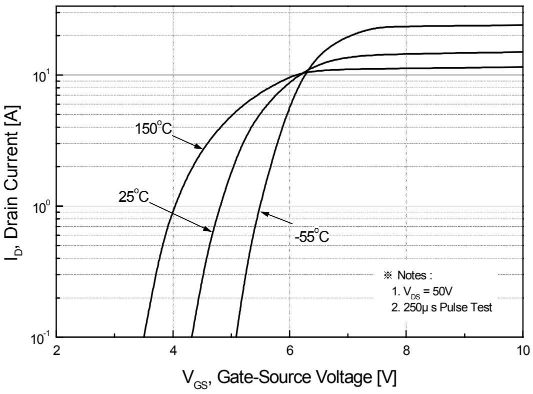


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

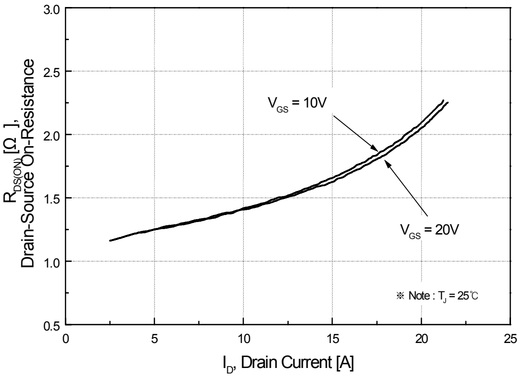


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

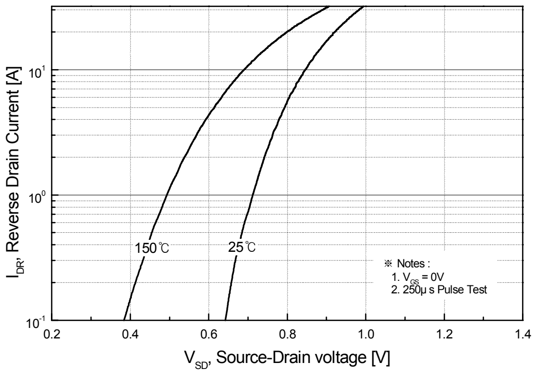


Figure 5. Capacitance Characteristics

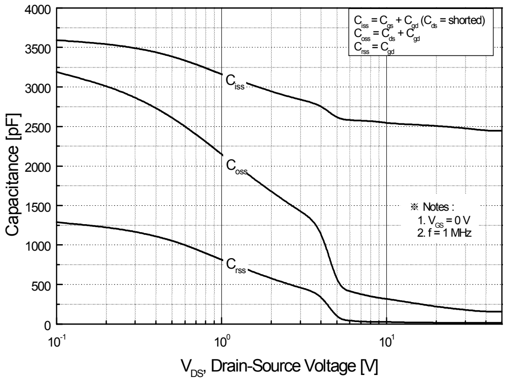
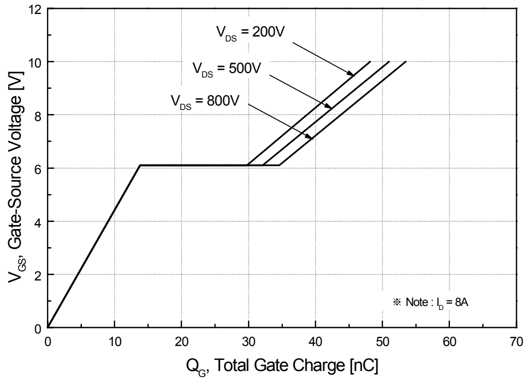
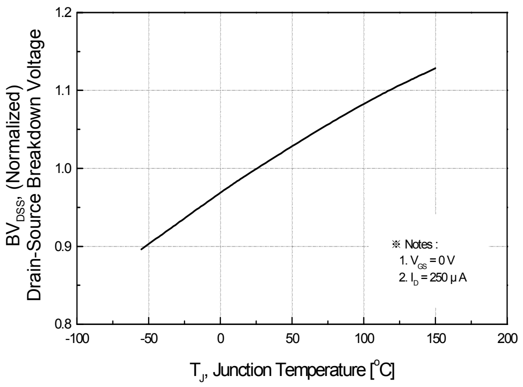


Figure 6. Gate Charge Characteristics



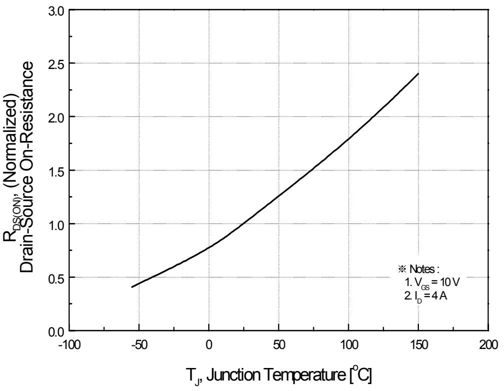
Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature



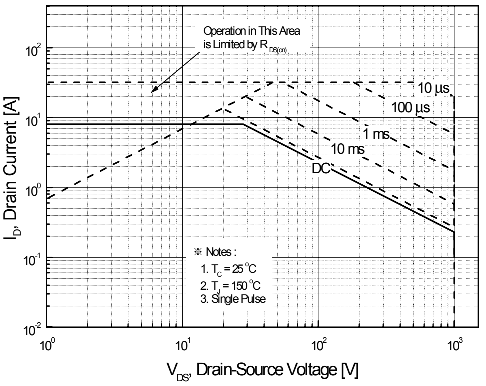
※ Notes :
1. $V_{GS} = 0$ V
2. $I_D = 250\ \mu A$

Figure 8. On-Resistance Variation vs. Temperature



※ Notes :
1. $V_{GS} = 10$ V
2. $I_D = 4$ A

Figure 9. Maximum Safe Operating Area



※ Notes :
1. $T_C = 25\ ^\circ C$
2. $T_J = 150\ ^\circ C$
3. Single Pulse

Figure 10. Maximum Drain Current vs. Case Temperature

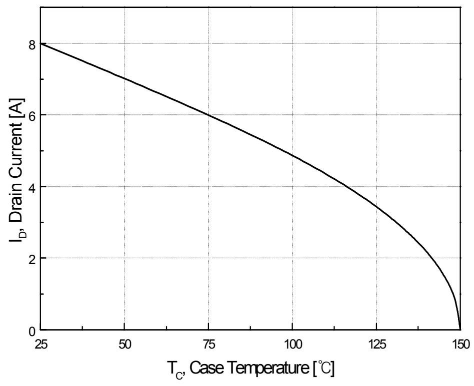
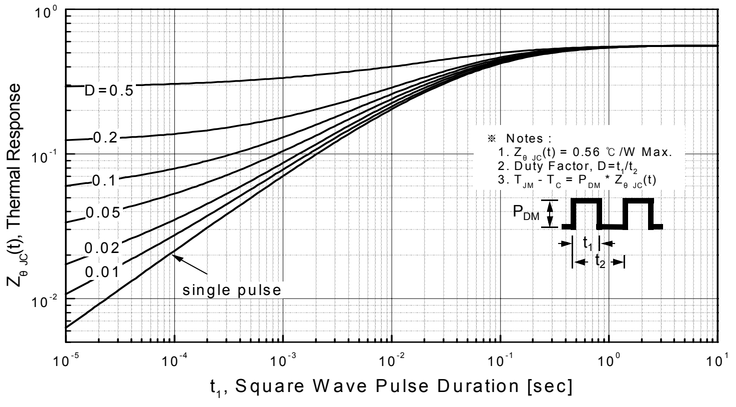
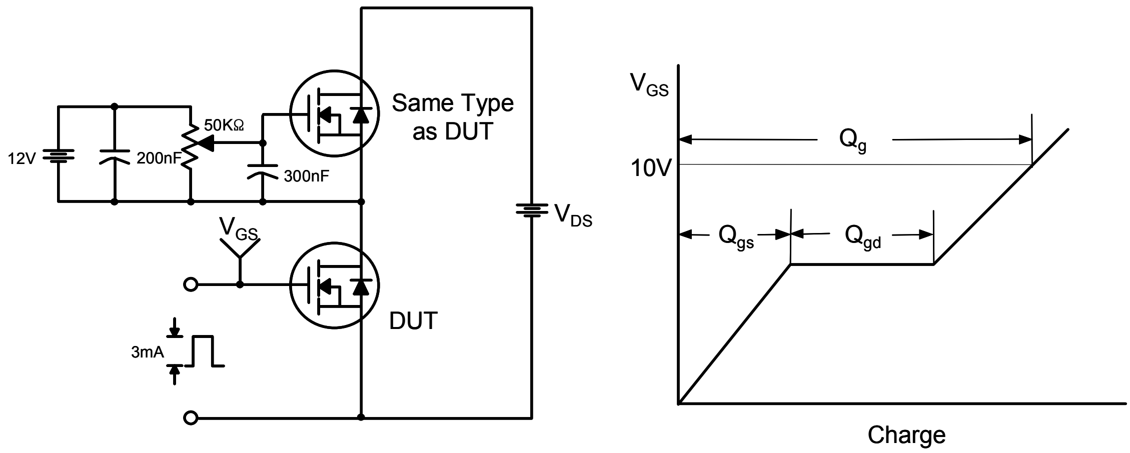


Figure 11. Transient Thermal Response Curve

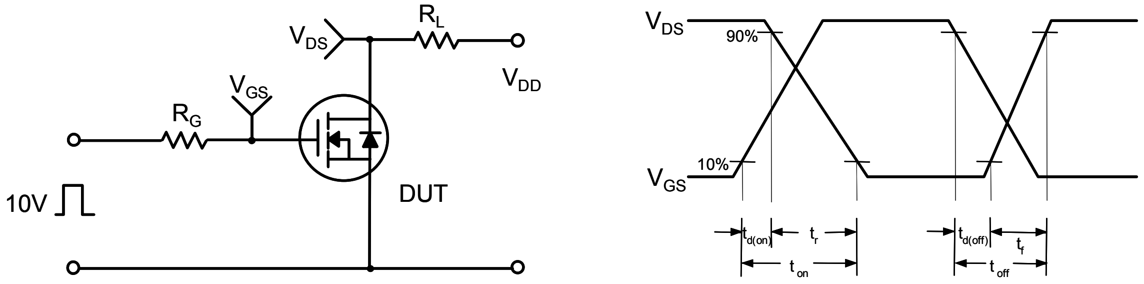


※ Notes :
1. $Z_{\theta JC}(t) = 0.56$ ℃/W Max.
2. Duty Factor, $D = t_1/t_2$
3. $T_{JM} - T_C = P_{DM} * Z_{\theta JC}(t)$

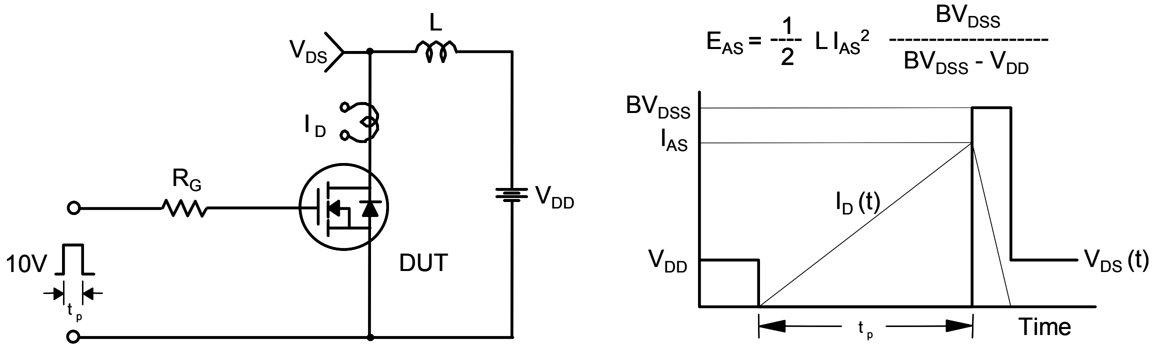
Gate Charge Test Circuit & Waveform



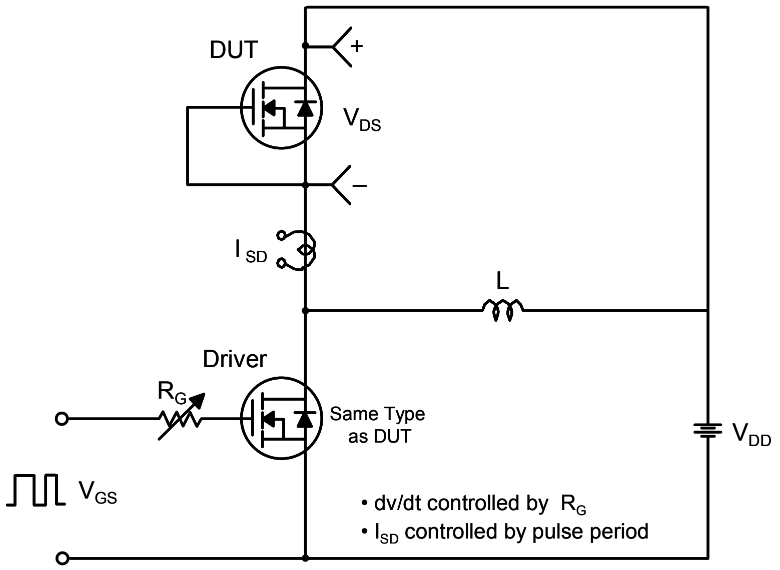
Resistive Switching Test Circuit & Waveforms

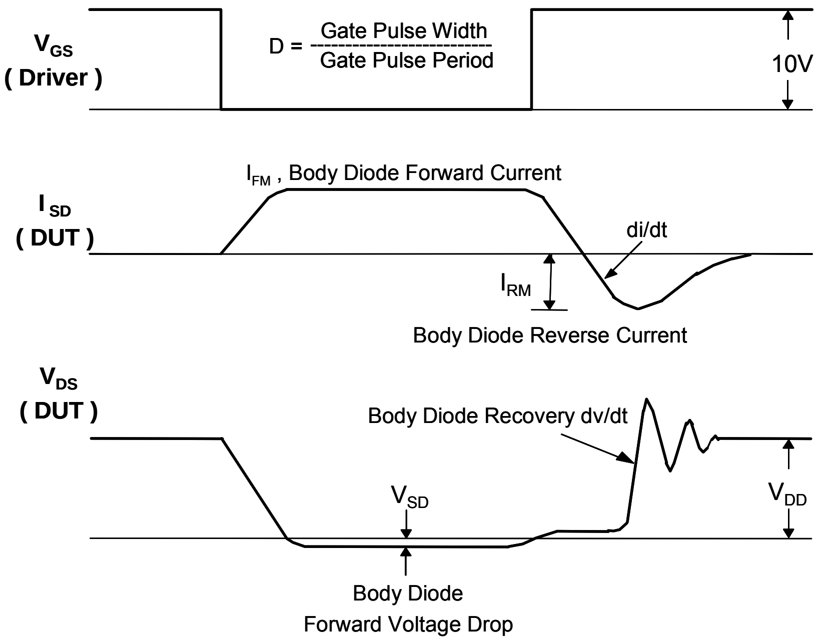


Unclamped Inductive Switching Test Circuit & Waveforms



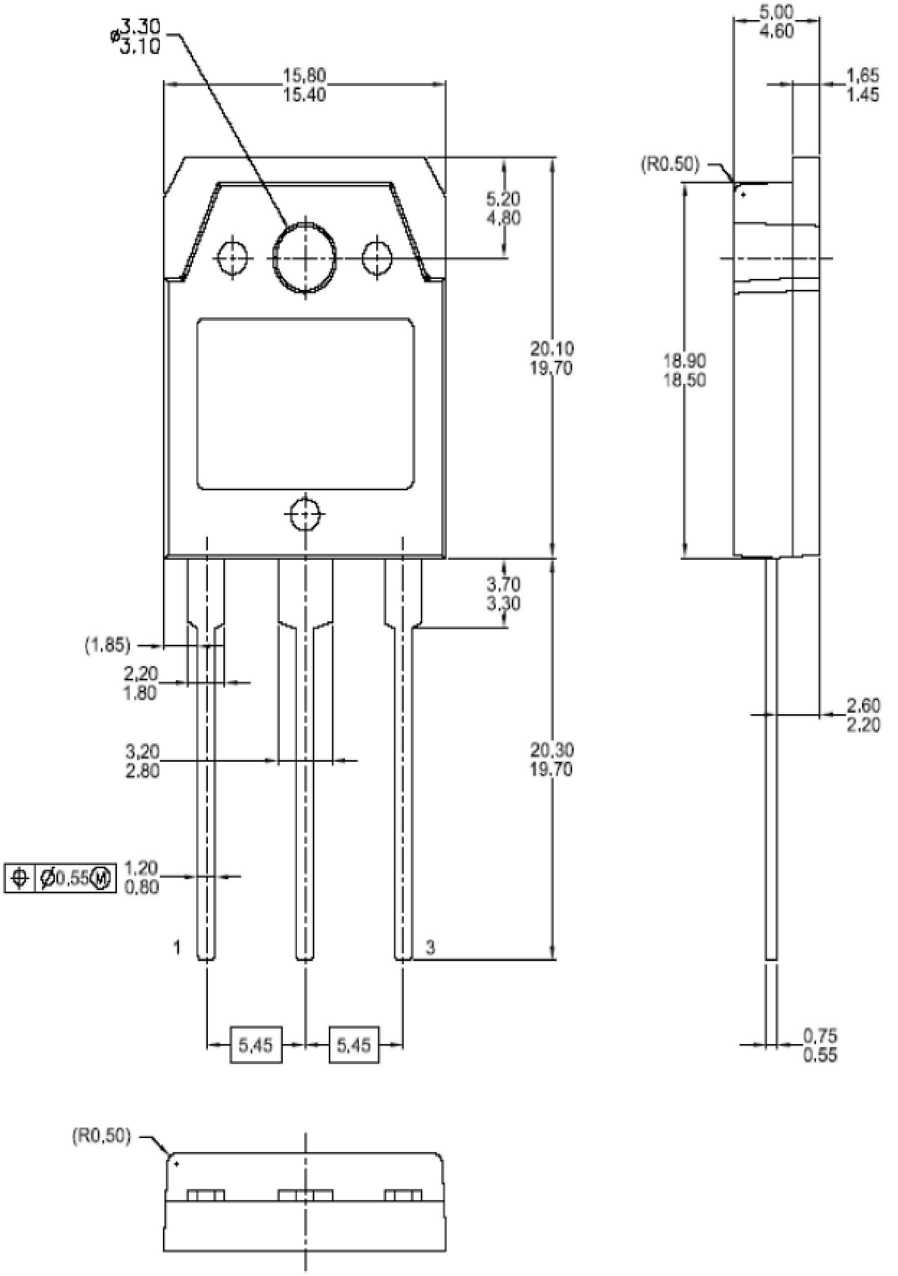
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

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